



#26/F  
501.36931X00  
Expedited Procedure Requested  
Amendment Under 37 CFR 1.116  
Group 2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: IWASAKI, et al.  
Serial No.: 09/255,856  
Filed: February 23, 1999  
For: SEMICONDUCTOR DEVICE WITH LAYERED  
INTERCONNECT STRUCTURE  
Group: 2813  
Examiner: S. Smoot

9/24/02  
3/28/03  
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Manual

AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner for Patents  
Box AF  
Washington, D.C. 20231

September 18, 2002

Sir:

In response to the Office Action mailed March 18, 2002, please amend the  
above-identified application as follows:

O.K. to  
Enter  
A.W.S.

IN THE CLAIMS:

Please amend the claims presently in the application as follows:

30. (Twice Amended) A semiconductor device having a layered  
interconnection structure including a copper film formed overlying a surface of a  
semiconductor substrate, and having a dielectric film overlying the surface of the  
semiconductor substrate, wherein the layered interconnection structure includes the  
copper film and a neighboring film adjacent the copper film, the neighboring film

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